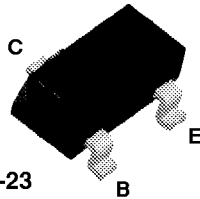


## BCV27



SOT-23  
Mark: FF

### NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	10	V
$I_C$	Collector Current - Continuous	1.2	A
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCV27	
$P_D$	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

\* Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

## NPN Darlington Transistor

(continued)

### Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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#### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ nA}, I_C = 0$	10			V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
$I_{EBO}$	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_C = 0$			0.1	$\mu\text{A}$

#### ON CHARACTERISTICS

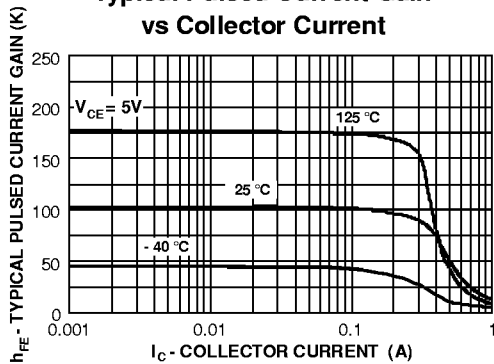
$h_{FE}$	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	4,000 10,000 20,000			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$			1.5	V

#### SMALL SIGNAL CHARACTERISTICS

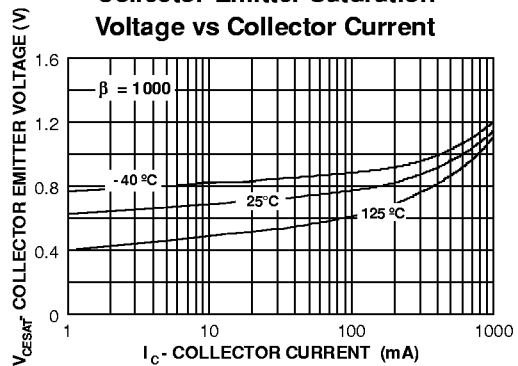
$f_T$	Current Gain - Bandwidth Product	$I_C = 30 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$		220		MHz
$C_C$	Collector Capacitance	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		3.5		pF

### Typical Characteristics

**Typical Pulsed Current Gain vs Collector Current**

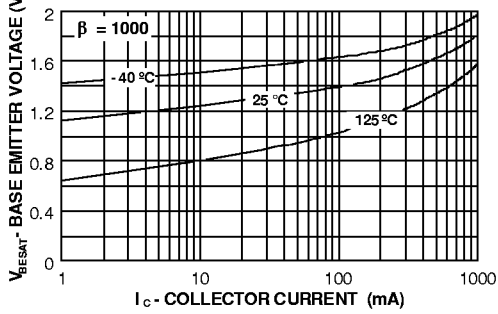


**Collector-Emitter Saturation Voltage vs Collector Current**

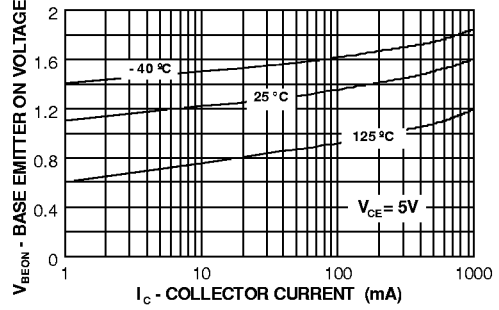


Typical Characteristics (continued)

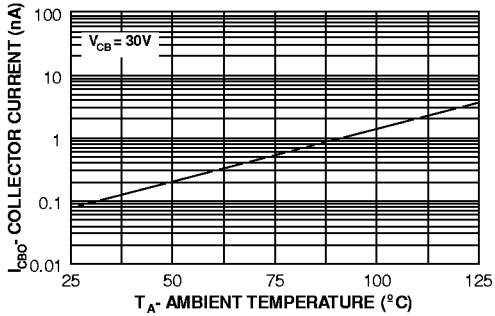
Base-Emitter Saturation Voltage vs Collector Current



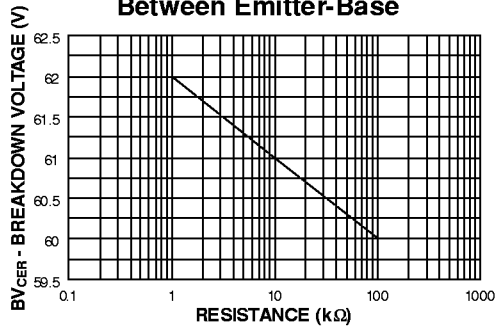
Base Emitter ON Voltage vs Collector Current



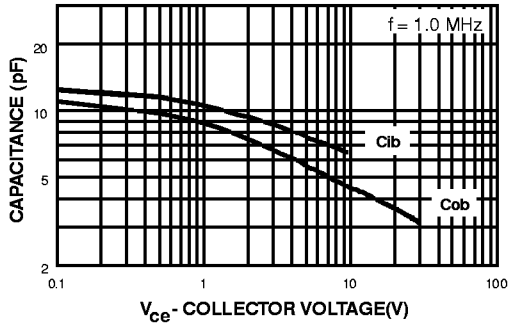
Collector-Cutoff Current vs Ambient Temperature



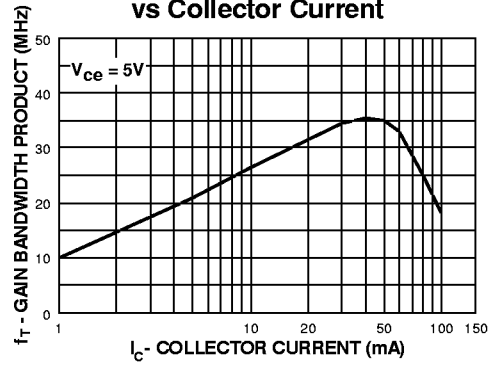
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



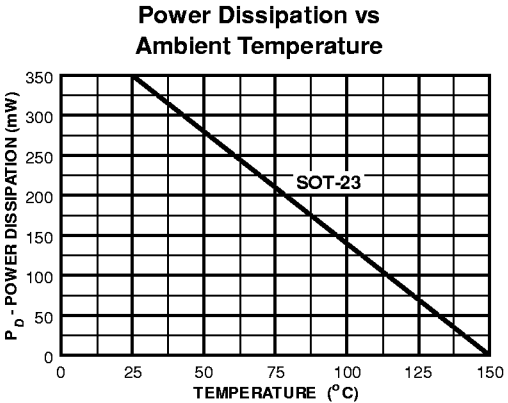
Input and Output Capacitance vs Reverse Voltage



Gain Bandwidth Product vs Collector Current



Typical Characteristics (continued)



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FAST®	SuperSOT™-3
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